

Including radiation damage effects in ATLAS Monte Carlo simulation: Status and perspectives

PSD13: The 13th International Conference of Position Sensitive Detectors

Oxford, 04.09.2023

Tobias Bisanz (TU Dortmund), on behalf of the ATLAS Collaboration

In hybrid pixel modules:

- Radiation effects on readout chips
	- Single event upsets in digital parts of readout chip
	- TID effects on transistor leakage current
- Radiation effects on sensor bulk
	- Change of effective doping concentration \rightarrow type inversion and change of depletion voltage
	- Loss of charge collection efficiency
	- Shift of Lorentz angle
	- In order to compensate: modify bias voltage and retuning
	- Disclaimer: we will not talk about effects on the readout chip

In hybrid pixel modules:

- Radiation effective readout
	- $Single$ event up arts of readout chip
	- TID effection transistor learage current
- Radiation effects on sensor bulk
	- Change of effective doping concentration \rightarrow type inversion and change of depletion voltage
	- Loss of charge collection efficiency
	- Shift of Lorentz angle
	- In order to compensate: modify bias voltage and $r \geq \log$
	- Disclaimer: we will not talk about effects on

the readout chip

The ATLAS Pixel Detector

- Four layer pixelated detector with three end–caps on each side
- Inner layer (IBL) was inserted later at about 3 cm distance from interaction point
	- IBL uses planar **200 µm thick** sensors with 250 µm x 50 µm pixel pitch
	- Most modules are **planar n⁺ -in-n**
	- Forward modules are **n + -in-p 3D sensors** $(230 \mu m)$ thick)
	- The innermost layer of the ATLAS Inner Tracker upgrade will use 3D sensors
	- Other Pixel layers and disks
	- Innermost is the B-Layer at $r = 5$ cm
	- **• 250 µm thick n⁺ -in n-sensors**
	- $400 \mu m \times 50 \mu m$ pixels

FBK: pass-through columns, p-spray isolation

Bump

isolated with p-stop implants

Radiation: present and future

- About 290 fb^{-1} of collisions delivered to ATLAS so far
- To IBL about 30 fb^{-1} less due to later installation
- We aim at 160 fb $^{-1}$ more for the rest of the project
- Innermost layers in the ATLAS Inner Tracker upgrade are targeted to withstand 2000 fb⁻¹ of radiation
- Conversion from integrated luminosity to fluence?

From luminosity to fluence

- No direct measurement of fluence • Measurement of luminosity and extrapolation to fluence • In forward region, leakage • Needs simulation of collisions (Pythia) and then transport code 2021 *JINST* **16** P08025 through the detector (FLUKA or C [mA/cm³] **ATLAS** Geant4) \sqrt{s} = 13 TeV Insertable B-layer 33.5 mm radius • Gives conversion from int. \overline{a} $|z| < 8$ cm luminosity to fluence $8 \text{ cm} < |z| < 16 \text{ cm}$ $6 cm = |z| > 24 cm$ $l cm < |z| < 32 cm / 3D$ senso
	- Indirect measurement of fluence by measurement of leakage current
		- Leakage current is proportional to fluence and voltage
		- Modelling of leakage current with Hamburg model

→ c.f. ATLAS Collaboration, 2021 *JINST* **16** P08025

current lower than expected

 $\Phi_{\text{neq}}^{\text{Si}}$ rate [10¹²/cm²/fb⁻¹]

- \rightarrow scale factors for IBL in z-bins
- (other layers are also scaled)
- **• large uncertainty due to this**

Modelling radiation damage

- Deposited charged by MIP in the sensor bulk drift to the electrodes due to electric field
	- Field is modified by radiation damage
- Path is deflected by magnetic field of 2 T solenoid + diffusion
	- Lorentz angle
- Charges can be trapped and only induce a fraction of signal
	- Ramo potential
- Digitisation step is used in many ATLAS Monte Carlo physics samples

→ c.f. ATLAS Collaboration, 2019 *JINST* **14** P06012

- Electric non-linear fields are simulated in TCAD for different fluences and bias voltages
	- Radiation damage modelled via **Chiochia model** for planar n-in-n sensors
	- For p-type bulk in 3D sensors, 3-level models (**Perugia*, LHCb****)
- *: F. Moscatelli et al., IEEE Trans. Nucl. Sci. 63 (2016) 2716
- **: A. Folkestad et al., NIM A874 (2017) 94-102

Input: ramo potential and charge trapping

 $0.6⁺$

 0.4

 $0.2⁺$

technische universität dortmund

- Ramo potential solved in TCAD
	- Only signal induced in adjacent pixels is considered (red box)
	- More complex potential for 3D sensors as the two n⁺-columns are electrically connected
- Charged are trapped (drawn from exponential distribution) and their induced charge at final position is computed
	- \sin Mean of exponential distribution $\frac{1}{2}$ 0.8

	1/($\beta\Phi$) with Φ the fluence
 $\beta_e = 4.5 \times 10^{-16} \text{ cm}^2 \text{ns}^{-1}$
 $\beta_h = 6.5 \times 10^{-16} \text{ cm}^2 \text{ns}^{-1}$
 $\frac{5}{2}$ 0.4
 $\frac{5}{2}$ 0.4
 $\frac{5}{2}$ 0.2
 $\frac{5}{2}$ 0.2 1/(βΦ) with Φ the fluence
	- $\beta_e = 4.5 \times 10^{-16} \text{ cm}^2 \text{ns}^{-1}$
	- $\beta_h = 6.5 \times 10^{-16} \text{ cm}^2 \text{ns}^{-1}$

- Cluster charge as measured in end of Run 2/early Run 3 data
- Comparison with radiation damage digitiser (and constant charge digitiser)
- **• Radiation damage digitiser replaces constant charge digitiser as ATLAS default since Run 3**
- **• Predicted most probable values match to 1%**

Charge collection efficiency

- Good prediction of charge collection efficiency for a large range of fluence
- Comparison of planar IBL and 3D IBL (difference fluence due to position) \rightarrow different radiation models, still good agreement
- Prediction within what we can deal with loss of CCE until end-of-life

Charge collection efficiency

- Good prediction of charge collection efficiency for a large range of fluence
- Comparison of planar IBL and 3D IBL (difference fluence due to position) \rightarrow different radiation models, still good agreement
- Prediction within what we can deal with loss of CCE until end-of-life

- Charge sharing also well modelled by radiation damage digitiser
- High number of pixels in a cluster in longitudinal direction because of forward position of 3D modules
- Even cumulative distribution of fraction of charge versus number of highest charge-pixels shows very good agreement

Digitiser: now and future

- Novel radiation damage digitiser used in ATLAS Monte Carlo production since Run 3
- Excellent agreement between data and MC predictions (w.r.t. large deviations with constant charge digitiser)
- For the ATLAS Inner Tracker (ITk) most inner layers: $(1 \text{ to } 2) \times 10^{16}$ 1 MeV n_{eq} /cm² after 2000 fb⁻¹
- current digitiser is unfortunately too slow
- \rightarrow need other approach for ITk
- ITk digitiser inspired by CMS template method → c.f. 2007 *PoS* **Vertex 2007** 035
- Lookup tables (LUTs) to determine how much charge induction is where and by how much it is reduced

Template method: allpix²

- Using the allpix² framework, the templates for the ITk digitiser are derived
- allpix² is a full Geant4 based detector simulation which simulates the propagation of charges in sensor bulk + further steps
- A LUT-based propagator based on the ITk digitiser approach has been implemented and is used to compare the "full" simulation vs. LUT approach

Template method: allpix²

- Using the allpix² framework, the templates for the ITk digitiser are derived
- allpix² is a full Geant4 based detector simulation which simulates the propagation of charges in sensor bulk + further steps
- A LUT-based propagator based on the ITk digitiser approach has been implemented and is used to compare the "full" simulation vs. LUT approach

- The new Run 3 radiation damage digiters performs well and is currently used in ATLAS MC production
- The agreement with Run 3 data is impressive
	- Also for the $3D$ n⁺-in-p pixel sensor
- Despite that, need for faster approach in the future \rightarrow ITk template approach
- This is currently under development and validation

- HV scans used to monitor depletion voltage with irradiation
- Shown are the data for the IBL 3Ds
- Increase MPV of cluster charge even above full depletion observed due to reduction of charge trapping
- Range between 0.2 to 6 x 10^{14} 1 MeV n_{eq} /cm² for given fluences

